12. The method according to any one of the preceding claims, wherein the base sheet (7) is made of a rigid material, such as PET and/or silicon and/or glass and/or SUS.

13. The method according to any one of the preceding claims, wherein the protective film (4) has a thickness in the range of 5 to 200 μm.

14. The method according to any one of the preceding claims, wherein the cushioning layer (13) has a thickness in the range of 20 to 300 μm.

15. A protective sheeting (5, 5') for use in processing a wafer (W), the protective sheeting (5, 5') comprising:

a base sheet (7);

a cushioning layer (13) applied to a front surface (17) of the base sheet (7);

a protective film (4), a back surface of which is attached to the cushioning layer (13); and

an adhesive layer (9) applied to at least part of a front surface of the protective film (4) opposite to the back surface thereof,

wherein the cushioning layer (13) is curable by an external stimulus, such as UV radiation, heat, an electric field and/or a chemical agent.

16. The protective sheeting (5, 5') according to claim 15, wherein the adhesive layer (9) has a substantially annular shape.

17. The protective sheeting (5, 5’) according to claim 16, wherein the inner diameter of the adhesive layer (9) is smaller than the diameter of a semiconductor-sized wafer (W).

18. The protective sheeting (5, 5’) according to claim 16 or 17, wherein the outer diameter of the adhesive layer (9) is larger than the inner diameter of a semiconductor-sized annular frame (25) for holding a semiconductor-sized wafer (W).